Amendments to the Claims

The claims in this listing will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1., 2. (Canceled)

3. (Currently Amended) A production method of a semiconductor wafer, comprising:

producing a semiconductor wafer by slicing a semiconductor ingot;

wrapping both surfaces of the semiconductor wafer;

etching both surfaces of the wrapped semiconductor wafer by bringing both surfaces of the wrapped semiconductor wafer in contact with etchant for removing distortion of both surfaces of the wrapped semiconductor wafer;

mirror polishing both surfaces of the etched semiconductor wafer;

clouding the step of etching a main one surface of a both-side the mirror finished polished semiconductor wafer by bringing the main one surface in contact with a sodium hydroxide solution, wherein a temperature is 80°C to 90°C and weight concentration is 60 wt% to 70 wt%, or a sodium hydroxide solution, wherein a temperature is 85°C to 90°C and weight concentration is 55 wt% to 60 wt% and by etching the one surface of the mirror polished semiconductor wafer for lowering a gloss level of the one surface of the mirror polished semiconductor wafer.

4. (Currently Amended) The production method of a semiconductor wafer as set forth in claim 3, furthermore further comprising:

the step of neutralizing by an acid solution the main one surface of the clouded semiconductor wafer contacted with said etchant by an acid solution after said etchant step clouding.

5. (Original) The production method of a semiconductor wafer as set forth in claim 4, wherein said acid solution contains ozone.

6. (Currently Amended) The production method of a semiconductor wafer as set forth in claim 4, <u>further comprising:</u>

<u>bringing the one surface of the neutralized semiconductor</u> ~~wherein a~~ wafer ~~surface is~~ ~~processed by using~~ <u>in contact with</u> an ozone solution after ~~the~~ neutralizing ~~step by said acid~~ ~~solution.~~